Abstracts

Ku-Band 10W High Efficiency HJFET Power Amplifier

K. Matsunaga, Y. Okamoto and M. Kuzuhara. "Ku-Band 10W High Efficiency HJFET Power Amplifier." 1995 MTT-S International Microwave Symposium Digest 95.2 (1995 Vol. II [MWSYM]): 335-338.

This paper describes a record power performance of a Ku-band power amplifier fabricated with a one-chip 0.45µm gate GaAs-based heterojunction FET (HJFET). The developed HJFET amplifier with 16.8mm gate periphery exhibited a 40.1 dBm(10.2W) output power with 50% power-added efficiency (PAE) and 9.5dB linear gain at 12GHz. This is the highest PAE, gain and output power combination achieved by a single FET power amplifier at this frequency.

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